

# MA6X129

## Silicon epitaxial planar type

For small power current rectification

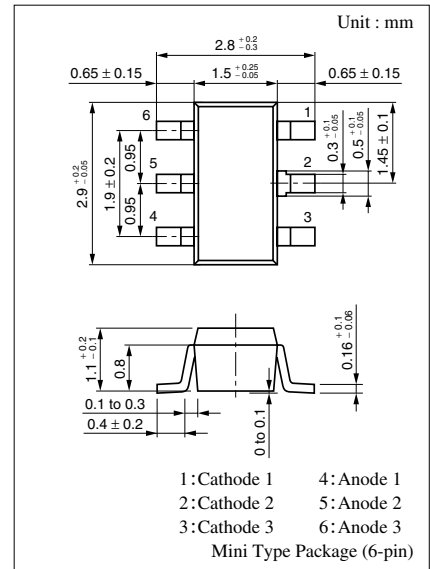
### ■ Features

- Three isolated elements contained in one package, allowing high-density mounting
- Allowing high voltage rectification

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

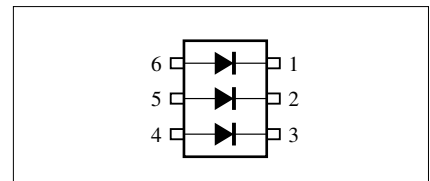
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Peak reverse voltage	$V_{RM}$	200	V
Output current	Single	$I_O$	100
	Triple		200
Repetitive peak forward current	Single	$I_{FRM}$	200
	Triple		600
Non-repetitive peak forward surge current*	Single	$I_{FSM}$	350
	Triple		1 000
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \* :  $t = 1 \text{ s}$



Marking Symbol: M4F

Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200 \text{ V}$			0.2	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 200 \text{ mA}$			1.2	V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		4.5		pF

Note) Rated input/output frequency: 3 MHz

